

In the Claims:

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims

1. (previously presented) An electrode structure on a p-type III group nitride semiconductor layer, comprising first, second and third electrode layers successively stacked on said semiconductor layer,

 said first electrode layer comprising at least one selected from a first metal group consisting of Hf, Zr, Nb, Ta and Sc,

 said second electrode layer comprising Co, and

 said third electrode layer comprising Au.

2. (original) The electrode structure according to claim 1, wherein said first electrode layer has a thickness in a range from 1 to 500 nm.

3. (original) The electrode structure according to claim 1, wherein said second electrode layer has a thickness of 5 nm or more.

4. (canceled)

5. (previously presented) The electrode structure according to claim 1, wherein said first electrode layer comprises a nitride of a metal included in said first metal group, and also comprises a compound of Ga and Co.

6-18. (canceled)

19. (original) An electrode structure on a p-type III group nitride semiconductor layer, comprising first, second and third electrode layers successively stacked on said semiconductor layer,

said first electrode layer comprising at least one selected from a first metal group consisting of Hf, Zr, Nb, Ta and Sc,

said second electrode layer comprising Ni, and

said third electrode layer comprising Au.

20. (original) The electrode structure according to claim 19, wherein said first electrode layer has a thickness in a range from 1 to 500 nm.

21. (original) The electrode structure according to claim 19, wherein said second electrode layer has a thickness of 5 nm or more.

22. (original) The electrode structure according to claim 19, wherein said first electrode layer comprises a nitride of a metal included in said first metal group, and also comprises a compound of Ga and Ni.

23. (original) An electrode structure on a p-type III group nitride semiconductor layer, comprising first, second and third electrode layers successively stacked on said semiconductor layer,

said first electrode layer comprising Hf, and said second electrode layer comprising at least one selected from a metal group consisting of Ni, Pd and Co, and

said third electrode layer comprising Au.

24. (original) The electrode structure according to claim 23, wherein said first electrode layer has a thickness in a range from 1 to 500 nm.

25. (original) The electrode structure according to claim 23, wherein said second electrode layer has a thickness of 5 nm or more.

26. (original) The electrode structure according to claim 23, wherein said first electrode layer comprises a nitride of a metal included in said first metal group; and also comprises a compound of Ga and a metal included in said metal group.

27. (previously presented) An electrode structure on a p-type III group nitride semiconductor layer, comprising first, second and third electrode layers successively staked on said semiconductor layer;

 said first electrode layer comprising a mixture containing a nitride of at least one selected from a first metal group consisting of Hf, Zr, Nb, Ta and Sc, and a Ga compound comprising Ni or Co,

 said second electrode layer comprising Ni or Co selected so as to form said Ga compound contained in said first electrode layer, and

 said third electrode layer comprising Au.

28. (original) The electrode structure according to claim 27, wherein said second electrode layer has a thickness of 5 nm or more.

29. (original) The electrode structure according to claim 27, wherein said third electrode layer has a thickness of 5 nm or more.